

MMBT6428LT1, MMBT6429LT1

Amplifier Transistors

NPN Silicon

Features

- Pb-Free Packages are Available

MAXIMUM RATINGS

Rating	Symbol	6428LT1	6429LT1	Unit
Collector–Emitter Voltage	V_{CEO}	50	45	Vdc
Collector–Base Voltage	V_{CBO}	60	55	Vdc
Emitter–Base Voltage	V_{EBO}	6.0		Vdc
Collector Current – Continuous	I_C	200		mAdc

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

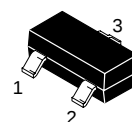
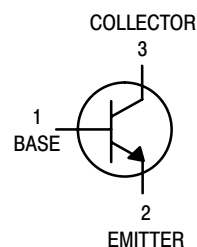
Rating	Symbol	Value	Unit
Total Device Dissipation FR–5 Board (Note 1) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	225 1.8	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction–to–Ambient	$R_{\theta JA}$	556	$^\circ\text{C}/\text{W}$
Total Device Dissipation Alumina Substrate, (Note 2) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	300 2.4	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction–to–Ambient	$R_{\theta JA}$	417	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature	T_J, T_{stg}	–55 to +150	$^\circ\text{C}$

- FR–5 = $1.0 \times 0.75 \times 0.062$ in.
- Alumina = $0.4 \times 0.3 \times 0.024$ in. 99.5% alumina.



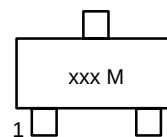
ON Semiconductor®

<http://onsemi.com>



SOT-23 (TO-236)
CASE 318
STYLE 6

MARKING DIAGRAM



xxx = Specific Device Code
MMBT6428LT1 – 1KM
MMBT6429LT1 – 1L
M = Date Code

ORDERING INFORMATION

Device	Package	Shipping†
MMBT6428LT1	SOT-23	3000 Tape & Reel
MMBT6428LT1G	SOT-23 (Pb-Free)	3000 Tape & Reel
MMBT6429LT1	SOT-23	3000 Tape & Reel
MMBT6429LT1G	SOT-23 (Pb-Free)	3000 Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector–Emitter Breakdown Voltage ($I_C = 1.0\text{ mA}$, $I_B = 0$) ($I_C = 1.0\text{ mA}$, $I_B = 0$)	$V_{(BR)CEO}$	50 45	– –	Vdc
Collector–Base Breakdown Voltage ($I_C = 0.1\text{ mA}$, $I_E = 0$) ($I_C = 0.1\text{ mA}$, $I_E = 0$)	$V_{(BR)CBO}$	60 55	– –	Vdc
Collector Cutoff Current ($V_{CE} = 30\text{ Vdc}$)	I_{CES}	–	0.1	μAdc
Collector Cutoff Current ($V_{CB} = 30\text{ Vdc}$, $I_E = 0$)	I_{CBO}	–	0.01	μAdc
Emitter Cutoff Current ($V_{EB} = 5.0\text{ Vdc}$, $I_C = 0$)	I_{EBO}	–	0.01	μAdc

ON CHARACTERISTICS

DC Current Gain ($I_C = 0.01\text{ mA}$, $V_{CE} = 5.0\text{ Vdc}$) ($I_C = 0.1\text{ mA}$, $V_{CE} = 5.0\text{ Vdc}$) ($I_C = 1.0\text{ mA}$, $V_{CE} = 5.0\text{ Vdc}$) ($I_C = 10\text{ mA}$, $V_{CE} = 5.0\text{ Vdc}$)	MMBT6428 MMBT6429 MMBT6428 MMBT6429 MMBT6428 MMBT6429 MMBT6428 MMBT6429	h_{FE}	250 500 250 500 250 500 250 500	– – 650 1250 – – – –	–
Collector–Emitter Saturation Voltage ($I_C = 10\text{ mA}$, $I_B = 0.5\text{ mA}$) ($I_C = 100\text{ mA}$, $I_B = 5.0\text{ mA}$)		$V_{CE(sat)}$	– –	0.2 0.6	Vdc
Base–Emitter On Voltage ($I_C = 1.0\text{ mA}$, $V_{CE} = 5.0\text{ Vdc}$)		$V_{BE(on)}$	0.56	0.66	Vdc

SMALL–SIGNAL CHARACTERISTICS

Current–Gain – Bandwidth Product ($I_C = 1.0\text{ mA}$, $V_{CE} = 5.0\text{ Vdc}$, $f = 100\text{ MHz}$)	f_T	100	700	MHz
Output Capacitance ($V_{CB} = 10\text{ Vdc}$, $I_E = 0$, $f = 1.0\text{ MHz}$)	C_{obo}	–	3.0	pF
Input Capacitance ($V_{EB} = 0.5\text{ Vdc}$, $I_C = 0$, $f = 1.0\text{ MHz}$)	C_{ibo}	–	8.0	pF

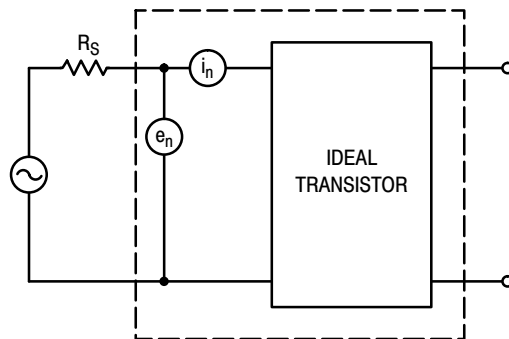


Figure 1. Transistor Noise Model

NOISE CHARACTERISTICS

($V_{CE} = 5.0 \text{ Vdc}$, $T_A = 25^\circ\text{C}$)

NOISE VOLTAGE

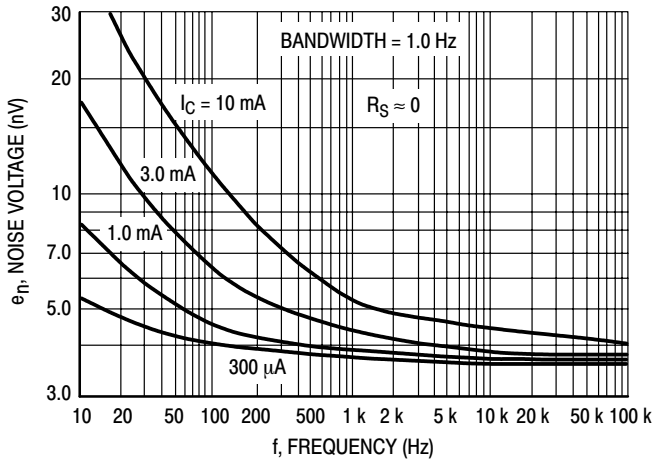


Figure 2. Effects of Frequency

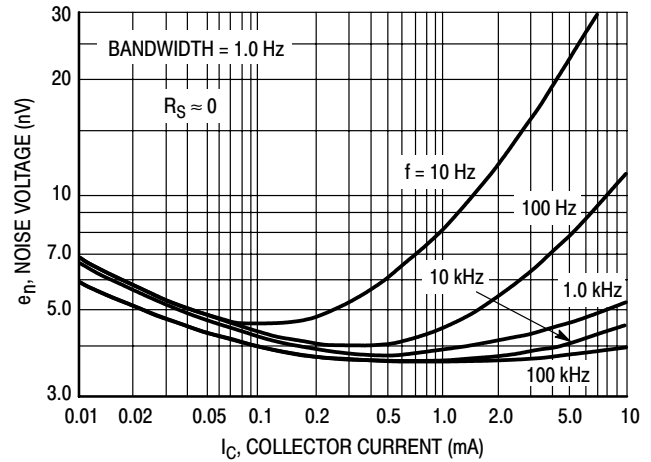


Figure 3. Effects of Collector Current

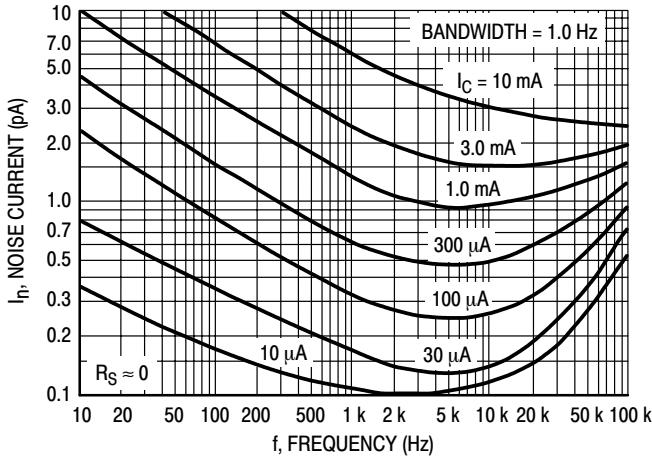


Figure 4. Noise Current

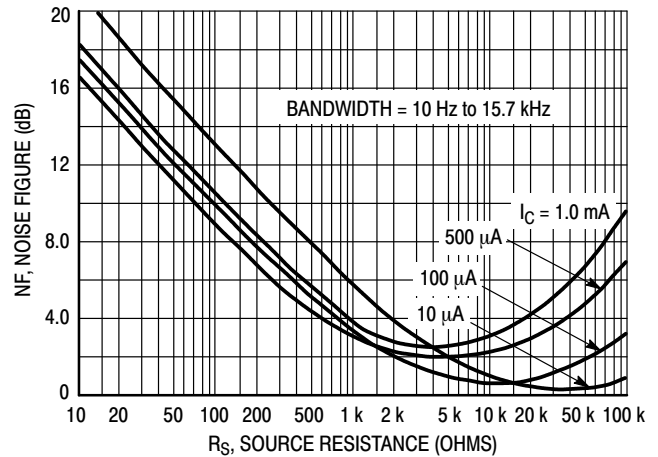


Figure 5. Wideband Noise Figure

100 Hz NOISE DATA

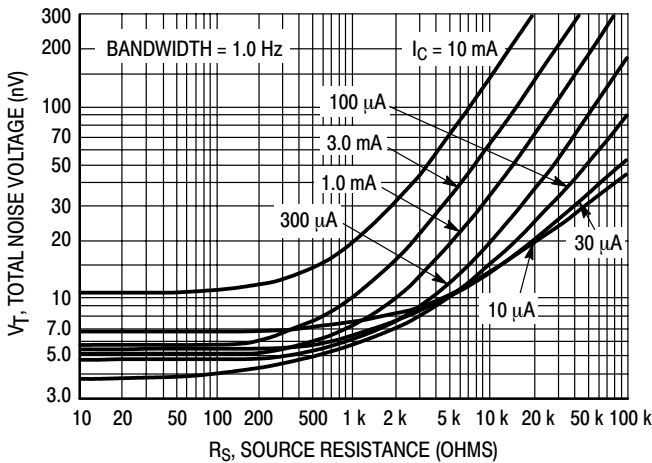


Figure 6. Total Noise Voltage

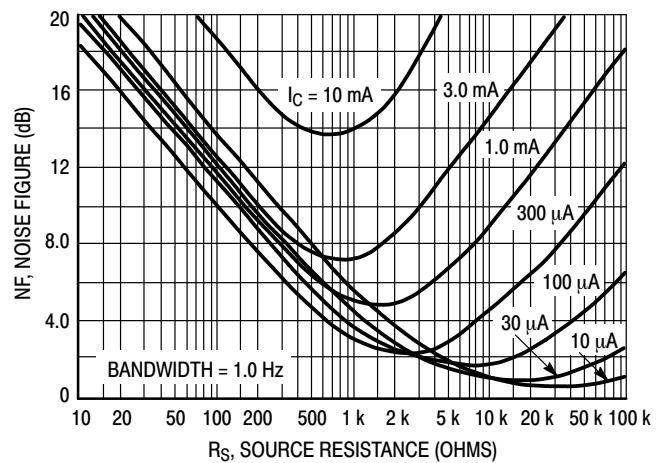


Figure 7. Noise Figure

MMBT6428LT1, MMBT6429LT1

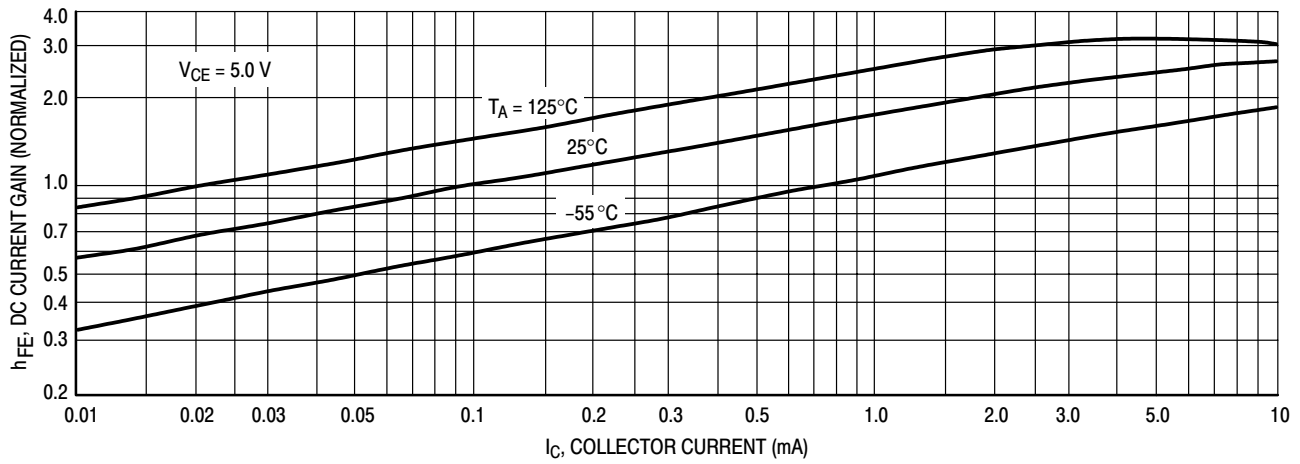


Figure 8. DC Current Gain

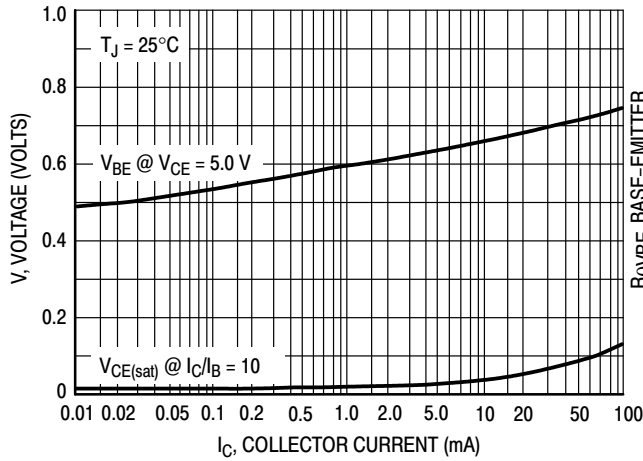


Figure 9. "On" Voltages

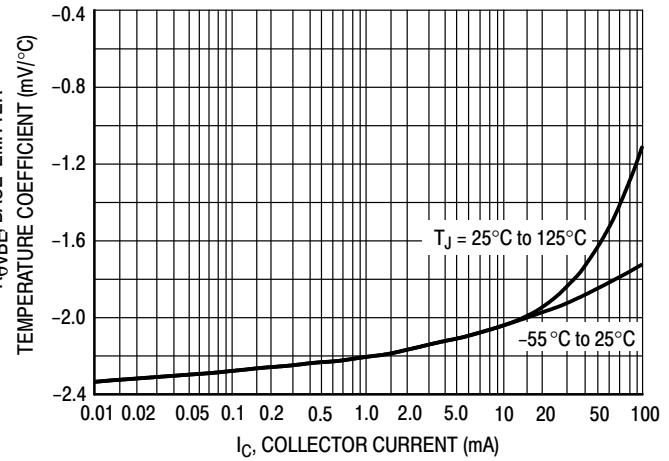


Figure 10. Temperature Coefficients

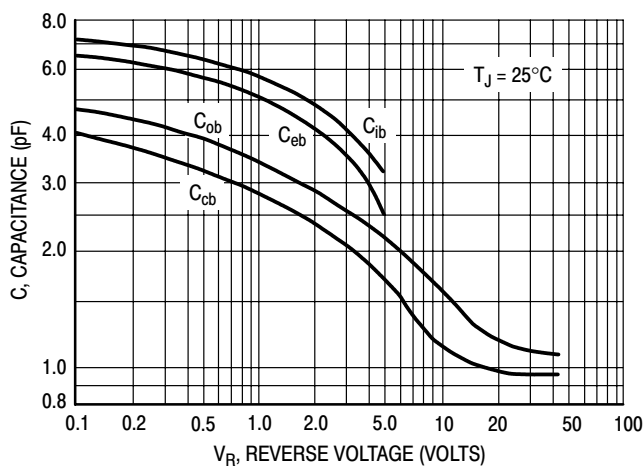


Figure 11. Capacitance

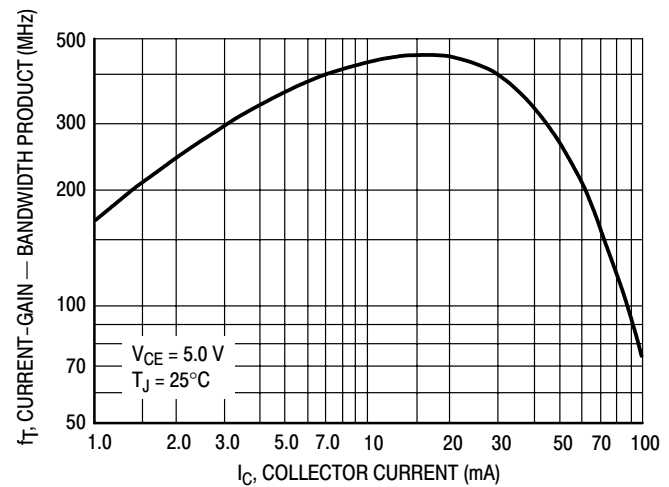
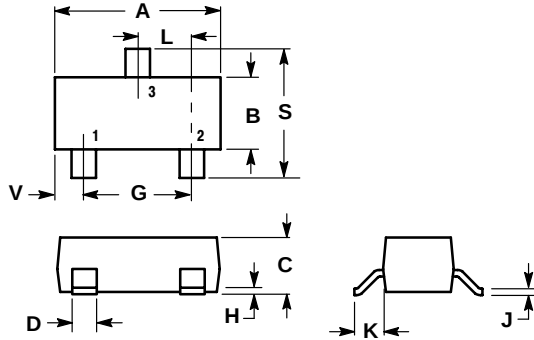


Figure 12. Current-Gain — Bandwidth Product

MMBT6428LT1, MMBT6429LT1

PACKAGE DIMENSIONS

SOT-23 (TO236)
CASE 318-18
ISSUE AK

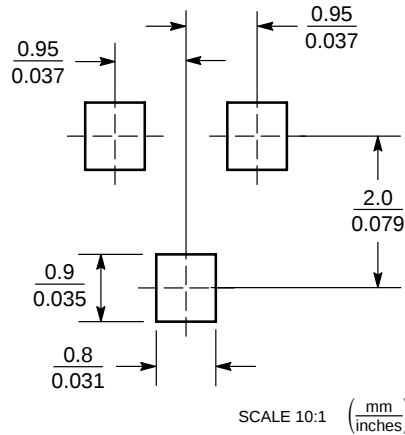


- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
 4. 318-01 THRU -07 AND -09 OBSOLETE, NEW STANDARD 318-08.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.1102	0.1197	2.80	3.04
B	0.0472	0.0551	1.20	1.40
C	0.0350	0.0440	0.89	1.11
D	0.0150	0.0200	0.37	0.50
G	0.0701	0.0807	1.78	2.04
H	0.0005	0.0040	0.013	0.100
J	0.0034	0.0070	0.085	0.177
K	0.0140	0.0285	0.35	0.69
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.1039	2.10	2.64
V	0.0177	0.0236	0.45	0.60

STYLE 6:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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